

VARIABLE EFFICIENCY FARADAY SHIELD

BACKGROUND OF THE INVENTION

[0001] The present invention relates generally to the field of electrical shielding. More particularly, the present invention relates to a Faraday shield for use with a plasma chamber.

[0002] Faraday shields have been used in plasma chambers to reduce capacitive RF coupling, which can result in ion erosion of chamber surfaces. A broad range of chamber materials is susceptible to this ion erosion problem: ceramic, quartz, SiN, SiC, plastics, etc. The Faraday shield is placed between RF antenna coils and the plasma containment chamber and reduces the amount of ion erosion of the chamber that is caused by RF electric field induced ion bombardment. The shield may be either grounded or floating.

[0003] A grounded shield design has the down side of making it very difficult to strike a plasma discharge in the chamber because reducing the capacitive coupling also reduces the magnitude of the RF electric field strength. However the grounded shield is effective for reducing ion erosion of the chamber. A floating shield design has the advantage that it does not interfere unduly with striking a plasma. Unfortunately, the floating shield is not very effective at preventing ion erosion of the chamber.

[0004] Referring to **Fig. 1**, an inductively coupled plasma etch reactor implementing a grounded Faraday shield **40** according to the prior art is illustrated. This reactor has a vacuum chamber **10** surrounded by an inductive coil **12**. A workpiece **14**, usually a semiconductor wafer, is supported inside the chamber **10** on a pedestal **16**. An inductive coil antenna **12** is wound around the outside of the chamber **10** and connected to a radio frequency (RF) power generator **18** through an impedance matching network **20** to provide RF power into the chamber. The chamber walls **30** in proximity to the antenna coil are composed of an electrically insulating material, typically quartz or ceramic, so as to minimize attenuation of the RF power coupled into the chamber **10**. Etchant gas is introduced into the chamber **10** through gas injection ports **26**. A vacuum pump (not shown) evacuates the chamber **10** to a desired chamber pressure.

[0005] The chamber dome 30 functions as an RF aperture. The Faraday shield 40 is effective at reducing process induced sputtering of the chamber dome 30. The Faraday shield 40 is connected to ground potential and is, thus, fully grounded.

[0006] Referring to Fig. 2, an inductively coupled plasma etch reactor implementing a floating Faraday shield 40' according to the prior art is illustrated. The floating (or "isolated") Faraday shield 40' is a known alternative to the fully grounded embodiment of Fig. 1. This approach is in widespread use on plasma chambers. Its performance is limited in comparison to what is achievable with a grounded design however.

[0007] These prior art Faraday shields 40, 40' reduce parasitic capacitive coupling between the antenna coils of inductively coupled plasma (ICP) sources and the contained plasma. The prior art shields are of a fixed efficiency design however.

[0008] Thus, what is needed is a Faraday shield that provides the efficiency of a fully grounded configuration, but that will not create the arc attenuation of a fully grounded configuration.

[0009] According to prior art nomenclature, the Faraday shield structures used in conjunction with a processing chamber have been referred to as a "voltage distribution electrode" (or VDE). However, because of significant structural distinctions, it may not be appropriate to use this older terminology for describing at least some embodiments according to the present invention.

SUMMARY OF THE INVENTION

[0010] One aspect of the present invention is reduction of the intensity of damaging ion-bombardment for certain semiconductor processing chamber surfaces, without affecting plasma striking capability.

[0011] Another aspect of the present invention is to provide a Faraday shield having a variable shielding efficiency.

[0012] Yet another aspect of the present invention is to control the rate of transition of a Faraday shield between fully ungrounded and fully grounded states.

- [0013] Still another aspect of the present invention is to control the rate of transition of a Faraday shield of a plasma reactor between a fully ungrounded state and a fully grounded state so as to maintain stable plasma conditions in the transitional period.
- [0014] A further aspect of the present invention is to control the time rate of change of the change in shielding efficiency of a Faraday shield at a predetermined rate.
- [0015] An additional aspect of the present invention is to control the time rate of change of change of shielding efficiency of a Faraday shield of a plasma reactor conditioned upon successful matching as the shield efficiency settings change.
- [0016] Another aspect of the present invention is to provide a variable efficiency Faraday shield having radial symmetry with pie shaped shield segments.
- [0017] Some of the above aspects are embodied by a shield that provides electrical shielding at a variable efficiency. The shield includes a substrate, a common node disposed on the substrate, and plural shield segments spaced apart from one another and being disposed on the substrate. The shield also includes plural switches, wherein each of the plural switches is connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node.
- [0018] Others of the above aspects are embodied by a shielding system that provides electrical shielding at a variable efficiency. The shield includes a substrate, a common node disposed on the substrate, and plural shield segments spaced apart from one another and being disposed on the substrate. The shield also includes plural switches, wherein each of the plural switches is connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node. The control interface includes a ground circuit connecting the common node to ground potential, and an incremental command circuit connected to each of the plural switches and generating command signals to selectively close the plural switches based upon occurrence of one or more conditions precedent.
- [0019] Certain of the above aspects are embodied by a plasma reactor which is useful in applying energized plasma to semiconductor articles. The plasma reactor includes a

reactor body (where at least a portion of the reactor body is formed of a dielectric material), an RF antenna disposed adjacent the reactor body, an RF matching network connected to the RF antenna to couple energy to the RF antenna, and a shield having variable shielding efficiency, disposed between the RF antenna and the reactor body. A semiconductor article disposed in the reactor body is processed by plasma that is energized by the RF antenna.

[0020] Some of the above aspects are embodied by a method of shielding. The shielding method includes providing a shield having a variable shielding efficiency, setting the shielding efficiency at a minimum value, and incrementally increasing the shielding efficiency of the shield.

[0021] Some of the above aspects are also embodied by a method of etching a semiconductor article. This method includes placing the semiconductor article in a plasma etch chamber and setting the shielding efficiency of a shield to a minimum value. A plasma is struck about the semiconductor article, and the shielding efficiency of the shield is then increased from the minimum value to a maximum value.

[0022] Another way of embodying some of the above aspects is a method of retrofitting a variable efficiency electrical shield to a semiconductor process chamber surrounded by an RF antenna. This method includes providing a variable efficiency electrical shield, installing the shield between the process chamber and the RF antenna, and interfacing the shield to a process controller to establish control of the efficiency of the shield.

[0023] Also according to the various embodiments of the present invention, the rate of transition between fully ungrounded and fully grounded states is controllable so as to maintain stable plasma conditions in the transitional period. With this novel approach, the time rate of change of the shielding efficiency is controlled at a predetermined rate once plasma strike is achieved, or is made conditional to successful matching at the previous shield setting.

BRIEF DESCRIPTION OF THE DRAWINGS

[0024] Additional objects and advantages of the present invention will be apparent in the following detailed description read in conjunction with the accompanying drawing figures.

- [0025] Fig. 1 illustrates a cross sectional schematic view of a plasma reactor according to the prior art, having a fully grounded Faraday shield.
- [0026] Fig. 2 illustrates a cross sectional schematic view of a plasma reactor according to the prior art, having an ungrounded Faraday shield.
- [0027] Fig. 3 illustrates plan view of a variable efficiency Faraday shield according to an embodiment of the present invention, situated between an RF antenna and a domed of a plasma chamber.
- [0028] Fig. 4 illustrates a perspective detail view of a portion of a variable efficiency Faraday shield according to the embodiment of Fig. 3.
- [0029] Fig. 5 illustrates a cross sectional detail view of a variable efficiency Faraday shield according to the embodiment of Fig. 3, situated with respect to various hardware of a plasma chamber.
- [0030] Fig. 6 illustrates a schematic view of a simplified variable efficiency Faraday shield according to an alternate embodiment of the present invention.
- [0031] Fig. 7 illustrates a schematic view of a variable efficiency Faraday shield according to another alternate embodiment of the present invention.
- [0032] Fig. 8 illustrates a schematic view of a variable efficiency Faraday shield according to yet another alternate embodiment of the present invention.
- [0033] Fig. 9 illustrates a perspective view of a variable efficiency Faraday shield according to still another alternate embodiment of the present invention.
- [0034] Fig. 10 illustrates a sectional view of a processing chamber with a flat top.
- [0035] Fig. 11 illustrates an exploded view of a variable efficiency Faraday shield according to a further alternate embodiment of the present invention.
- [0036] Fig. 12 illustrates a method of etching a semiconductor article according to an embodiment of the present invention.
- [0037] Fig. 13 illustrates a method of increasing shielding efficiency according to one alternate embodiment of the present invention.

[0038] Fig. 14 illustrates a method of increasing shielding efficiency according to another alternate embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0039] An ungrounded passive voltage distribution electrode (VDE) is commonly interposed between the excitation antenna coils and the RF dome in an etch chamber. This VDE is an example of an application-specific ungrounded Faraday shield.

[0040] As discussed above, a grounded shield is more effective at minimizing the capacitive coupling between the excitation antennae and the chamber plasma, and therefore in reducing the plasma potential difference between the bulk of the plasma and the inner surface of the RF aperture. By reducing the plasma potential in this location, the sputter erosion rate of the ceramic material of the aperture is significantly reduced.

[0041] Unfortunately, a grounded shield design has the downside of making plasma strike difficult in the chamber, and can cause the impedance of the aggregate antenna circuit fall outside of the nominal range of the tuning network. This is the principal reason why the more effective grounded design has not been incorporated into prior art plasma chamber designs.

[0042] The present invention obtains the functionality of both the ungrounded and the grounded prior art shield configurations, without an abrupt change between the two.

[0043] A shield according to an embodiment of the present invention is situated between the RF antennae of an Inductively Coupled Plasma (ICP) source and the RF aperture of an inductively coupled semiconductor processing chamber. The invention has a compact design, and can be added to a pre-existing chamber without the need for extensive mechanical or RF redesign. According to a preferred embodiment of the present invention, a shield apparatus is constructed that has a Faraday shield design which is divided into numerous independent "pie slice" segments, each switchable to ground potential.

[0044] According to one aspect of the present invention, the rate at which the shield segments are grounded can be precisely controlled, so that the ungrounded-to-grounded transition occurs at a rate at which existing RF matching network can track and maintain optimal power coupling into the plasma. Another aspect of the present invention is that

the Faraday shield apparatus includes structure for shielding of critical control and switching elements to allow the Faraday shield to operate reliably in an RF hot environment.

[0045] A very useful aspect of the present invention is that the rate of increase of the shielding efficiency is an adjustable parameter. Thus, the rate of change of shield efficiency is adaptable so as to match the finite match tuning rates for a given plasma chamber.

[0046] Referring to **Fig. 3**, a plan view of a variable efficiency Faraday shield **300** according to an embodiment of the present invention is illustrated. The Faraday shield **300** is situated between an RF antenna **312** and a dome **330** of a plasma chamber.

[0047] The Faraday shield **300** is divided into numerous independent "pie slice" shaped segments **320**. Each of the shield segments **320** is switchable to ground potential via a corresponding switch **340**. The switch **340** selectably connects its respective shield segment **320** to a grounded circuit on a flexible circumferential segment **350**. Because of the switchability, the shield **300** is actively adjustable rather than being a passive device with a single transfer characteristic.

[0048] The individual shield segments **320** and the circumferential segment **350** are formed using flexible circuit technology, and the switching **340** and control electronics **360** are surface mounted directly to the circumferential segment **350** structure. The grounded circuit on the circumferential segment **350** is preferably structured to incorporate grounded elements (not shown) that provide a high degree of RF noise isolation to the control electronics **360** that drive the switching electronics **340** and to the control signal input lines. It is also preferred that the shield segments **320** and the circumferential segment **350** share a common flexible substrate.

[0049] Referring to **Fig. 4**, a perspective detail view of a portion of the variable efficiency Faraday shield **300** according to the embodiment of Fig. 3 is illustrated. According to this embodiment, sets of segments are grouped, or activated simultaneously, to reduce the total number of addressable shielding levels to a manageable number. This embodiment has five groupings **321, 322, 323, 324, 325** of electrode segments **320** so as to give selectable shielding at six levels, i.e., 0, 20, 40, 60, 80 and 100% of the maximum value. The

members of each grouped set **321, 322, 323, 324, 325** of co-activated segments are radially distributed so that they form eight (in this embodiment) platoons **327** that consist of one segment from each set **321, 322, 323, 324, 325**.

[0050] According to an alternate embodiment, the switch **340** corresponding to each and every single shield segment is independently addressable so that each shield segment **320** is independently switchable. This provides for much finer resolution of shield efficiently variation and produces the maximum operational flexibility. On the other hand, this maximizes the complexity of addressing the switches **340**.

[0051] Interconnections **352, 354** between the switch control electronics elements **360** run circumferentially and are collected at a single interfacing connector **370**, which interfaces to the system controller (not shown in this view).

[0052] An optional feature of the Faraday shield are the thinned portions **356** of the circumferential segment **350**. The thinned portions **356** provide adaptability of size and shape so that a single Faraday shield configuration is useable for chamber lids and domes having a range of diverse sizes and shapes. The thinned portions **356** need only be wide enough to bear the grounding lines and the signal lines **352, 354** running between all the driver circuits **360**.

[0053] The driver circuits **360** are exemplified as five channel multiplexed driver chips. The type of driver chip is based on the type of device that is used to embody the switches **340**. When PIN diodes are chosen for switches **340**, a suitable choice for the driver circuits **360** is a Decoded PIN Driver sold under the designation "DS Series" by Impellimax of 375 West Hollis Street, Nashua, NH 03060.

[0054] Referring to **Fig. 5**, a cross sectional detail view of a variable efficiency Faraday shield **300** according to the embodiment of Fig. 3 is illustrated. The Faraday shield **300** is shown situated with respect to various hardware of a plasma chamber. The shield segments **320** of the Faraday shield **300** are disposed between the antenna coil **312** and the dome **330**.

[0055] A clamp ring **532** engages the dome **330** circumferentially. A TEFLON™ ring **534** rests on the clamp ring **532** and the edge of the dome **330** to hold the flexible Faraday shield **300** in place about its circumference. The interfacing connector **370** is coupled via

a flat flexible interface cable **375**, which wraps under and around the TEFLON™ ring **534** and connects to the circuitry of the Faraday shield **300**.

[0056] One aspect of the present invention is that each segment **320** of the shield **300** is connected to the grounded circuit on the circumferential segment **350** through a switch **340**. The switch **340** may be embodied as a switchable PIN diode, and may alternately be embodied as an equivalent device. Each of these switches **340** is controlled by driver circuitry **360**. When the switches **340** are embodied as PIN diodes, the driver circuitry **360** is preferably a PIN diode driver chip.

[0057] Referring to **Fig. 6**, a schematic view of a simplified variable efficiency Faraday shield **610** according to an alternate embodiment of the present invention is illustrated. The efficiency of a single plate Faraday shield **610** is made variable by coupling the shield to ground via a switch **620** that enables the shield to be selectively connected to or disconnected from ground potential.

[0058] When this shield structure is employed, a plasma arc is struck when the Faraday shield **610** is switched to its floating state. Then the switch **620** is closed to ground the Faraday shield **610** once a stable plasma has been established.

[0059] Under certain circumstances, this shield configuration provides a satisfactory solution to the plasma strike vs. dome etch dilemma of the prior art. That is because it is possible, albeit difficult for some geometries, to maintain the plasma when the shield is switched from a floating state to a fully grounded state. When the shield is switched from a floating state to a grounded state, this substantially changes the electrical impedance seen at the RF antenna (not shown in this view). The RF match network (not shown in this view) must adapt quickly enough to the sudden change in impedance to prevent power transfer efficiency dropping too much. This embodiment is not preferred in some circumstances, though, because potential instability in power transfer may tend to destabilize and extinguish the plasma.

[0060] Referring to **Fig. 7**, a schematic view of a variable efficiency Faraday shield **710** according to another alternate embodiment of the present invention is illustrated. The efficiency of a single plate Faraday shield **710** is made variable by coupling the shield **710** to ground via a variable impedance element **720**. The variable impedance element **720**

may take on an impedance value Z that has either a capacitive or inductive component at the RF excitation frequency, or that is purely resistive. The magnitude of the impedance value Z of the variable impedance element 720 may be varied from a maximum value all the way down to zero (i.e., a short circuit).

[0061] When the shield structure according to this embodiment is employed, a plasma arc is struck when the Faraday shield 710 is in a high impedance state, being essentially floated by having the impedance value Z of the variable impedance element 720 set at a high magnitude. Once a stable plasma has been established, the impedance value Z is gradually reduced in magnitude.

[0062] Implementation of a Faraday shield combined with an impedance structure according to this embodiment would be effected in a configuration similar to that of the embodiment of Fig. 4, with one or more impedance elements substituted in place of the switches 340.

[0063] Referring to Fig. 8, a schematic view of a variable efficiency Faraday shield 810 according to yet another alternate embodiment of the present invention is illustrated. The efficiency of a multiple segment Faraday shield 810 is made variable by permitting any or all of the shield segments 812, 814, 816, 818 to float, and selectively coupling any or all of the shield segments 812, 814, 816, 818 to ground via an impedance element 820 (having an impedance Z) or a direct connection 830. Switching for selective connection of the shield segments to either the impedance element or directly to ground is effected by tandem driver circuits 840, 842. The tandem driver circuits 840, 842 are controlled by control lines 850 to select which shield segments 812, 814, 816, 818 are to float, which are to connect to ground via the impedance element, and which are to connect to ground directly. Any connection combination is possible utilizing the circuit configuration illustrated, thus enabling choice of a myriad of possible shielding efficiencies. The number of shield segments shown is merely illustrative and is not intended to be limiting.

[0064] Referring to Fig. 9, a perspective view of a variable efficiency Faraday shield 910 according to an alternate embodiment of the present invention is illustrated. The shield 910 has plural segments 920 that are disposed across the top of a flat top chamber 930. The segments 920 are selectably switchable from floating state to ground state by driver

circuits **940, 942**. Application of the present invention is certainly not limited to domed chambers, nor to shield configurations having radial symmetry.

[0065] Referring to **Fig. 10**, a sectional view of a processing chamber **1010** with a flat top is illustrated. A variable efficiency Faraday shield **1020** is disposed above the dielectric shield **1012**. A plasma is formed in the space **1014** above wafer **1030** to be processed. The plasma is energized by the RF antenna **1040** disposed above the variable efficiency Faraday shield **1020**.

[0066] Also illustrated via a block diagram portion of **Fig. 10** is how the variable efficiency Faraday shield **1020** is integrated into a shielding system **1000**. The shield **1020** is connected to a control interface **1050** that provides grounding and command signals. Switches in the shield **1020** are controlled by command signals received from an incremental command circuit **1052**. The command signals are issued based on conditions precedent, such as the passage of time or an indication of an RF match by an RF match network. As the switches in the shield **1020** are closed, segments of the shield **1020** are connected to a ground circuit **1054**.

[0067] Referring to **Fig. 11**, an exploded view of a variable efficiency Faraday shield **1100** according to a further alternate embodiment of the present invention is illustrated. A shield according to this embodiment has multiple shield segments **1110, 1130, 1150** layered on top of one another, the separate layers of conductive shield segments **1110, 1130, 1150** being isolated from one another by non-conductive layers **1120, 1140**. Each of the shield segments **1110, 1130, 1150** is independently, selectably connectable to ground, either directly or via an impedance element. In practice the shield segments **1110, 1130, 1150** and the non-conductive layers **1120, 1140** are sandwiched together rather than being spaced apart as shown in this exploded view. Circuitry for selectably connecting the shield segments to ground is not shown, but is preferably implemented as described elsewhere in this description, in regard to other embodiments. When the lowest shield efficiency is desired, all of the shield segments **1110, 1130, 1150** are disconnected so that they float.

[0068] The bottom shield segment **1150** has narrow spoke-shaped radial members **1152** in a configuration having radial symmetry. When it is desired to increment the efficiency of

the shield **1100** above the lowest level, the bottom segment **1150** alone is connected to ground with the remaining segments **1110**, **1130** left floating.

[0069] The middle shield segment **1130** has radial members **1132** of an intermediate width in a configuration having radial symmetry. The radial members **1132** of the middle layer **1130** preferably overlap those of the bottom layer **1150**. Grounding the middle shield segment **1130** further increases the shielding efficiency of the shield **1100**.

[0070] The uppermost shield segment **1110** has wide pie slice-shaped radial members **1112** in a configuration having radial symmetry. The radial members **1112** of the uppermost layer **1110** preferably overlap those of the middle and bottom layers **1130**, **1150**. Grounding the uppermost shield segment **1110** increases the shielding efficiency of the shield **1100** to a maximum level.

[0071] Although this embodiment of the shield **1100** has been illustrated as having three layered segments, the shield is optionally implemented with only two layers to increase simplicity, or with four or more layers to permit smaller incremental changes in shielding efficiency. Although radial symmetry is preferred (so as to promote homogeneity of the plasma inside the chamber), implementations of the invention according to this embodiment are not limited to the specific shapes (e.g., spoke-shaped, pie-slice shaped) that have been described. The number and relative size of the radial members illustrated is not a critical aspect of the invention. For example, the radial members **1152** of the bottom segment **1150** may be configured having varying lengths (e.g., alternating long and short).

[0072] Process aspects of the present invention are illustrated via **Figs. 12 to 14**.

[0073] Referring to **Fig. 12**, after a workpiece (i.e., a semiconductor wafer) is placed in the plasma chamber **1210**, the system controller provides signals such that in the plasma strike phase **1230** of a process, all shield elements are ungrounded (i.e., floating) **1220**. Immediately after plasma strike **1230**, and with successful match tuning to minimal reflected power, the shield controller begins to ground the shield segments **1240**, ultimately grounding all the segments to obtain a maximum shield efficiency.

[0074] Referring to **Fig. 13**, the shield segments are grounded by increasing the total number grounded at a predetermined rate. After making an incremental increase in the shield efficiency **1310**, no additional increment is made until a predetermined time delay

1330, unless of course, it is determined 1320 that the maximum efficiency (all segments grounded) has been reached.

[0075] Referring to Fig. 14, an alternate method for increasing shielding efficiency is illustrated. The shield controller may increase the total number of grounded segments, conditionally, with successful match tuning 1430 gating 1440 the next increase 1410 to the total number grounded 1420.

[0076] A Faraday shield embodied according to the present invention is easy to manufacture. The segmented shield lends itself to an implementation that is easily realized with standard manufacturing techniques for flexible circuits with surface mounted electronic components.

[0077] In addition to reducing wear on chamber components, an additional advantage of the present invention is that it reduces the amount of on-wafer and on-chamber contamination by reducing the rate of sputtering of certain ceramic chamber surfaces.

[0078] Furthermore, the present invention reduces the rate of sputtering in a controllable manner after plasma strike has been successfully executed. Reduction is accomplished by incrementally and rapidly grounding successively more elements of an optimized, segmented, Faraday shield design, until the entire shield is grounded. The Faraday shield has maximum shielding efficiency when entirely grounded. Alternatively, the shielding efficiency is increased by reducing the impedance to ground for the segments, until the segments are virtually grounded.

[0079] A variable efficiency shield offers significant advantages over fixed designs, by offering a method of varying the capacitive component of coupling from the antenna to the plasma, and accommodating a wide range of plasma conditions without a redesign to the existing RF hardware.

[0080] The “pie shaped” configuration of the shield segments is not essential to the practice of the invention, nor is the number of segments disclosed, nor are the grouping or platoon patterns. The number and geometric configuration of the shielding segments are preferably chosen so as to provide optimum shielding performance based on the shape of the plasma reactor for which the shield is being tailored. The useful aspects and

advantages of the present invention may be extended to any geometry to work with a plasma reactor of any size, shape, or configuration.

[0081] The present invention has been described in terms of preferred embodiments, however, it will be appreciated that various modifications and improvements may be made to the described embodiments without departing from the scope of the invention.

WHAT IS CLAIMED IS:

1. A shield for providing electrical shielding at a variable efficiency, the shield comprising:
 - a common node;
 - a single unitary shield element; and
 - a variable impedance element connected between the common node and the shield segment.
2. The shield of claim 1, wherein the impedance of the variable impedance element is variable.
3. The shield of claim 1, wherein the impedance of the variable impedance element varies according to discrete values.
4. The shield of claim 3, wherein the variable impedance element comprises a switch.
5. A shield for providing electrical shielding at a variable efficiency, the shield comprising:
 - a common node;
 - plural shield segments spaced apart from one another; and
 - plural switches, each of the plural switches being connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node.
6. The shield of claim 5, further comprising:
 - multiplexing circuitry disposed on the substrate and connected to each of the plural switches to control opening and closing of the switches.
7. The shield of claim 5, wherein each of the plural switches is indirectly connected to the common node via an impedance element, so that closure of each switch connects its respective one of the plural shield segments to the common node via the impedance element.

8. The shield of claim 5, wherein the plural shield segments are arranged radially in a “pie slice” configuration.

9. The shield of claim 8, wherein the common node extends circumferentially about the radially-arranged plural shield segments.

10. A shielding system for providing electrical shielding at a variable efficiency, the shielding system comprising:

- a shield; and

- a control interface connected to the shield;

- wherein the shield comprises:

- a common node;

- plural shield segments spaced apart from one another; and

- plural switches, each of the plural switches being connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node; and

- wherein the control interface comprises:

- a ground circuit connecting the common node to ground potential; and

- an incremental command circuit connected to each of the plural switches and generating command signals to selectively close the plural switches based upon occurrence of one or more conditions precedent.

11. The shielding system of claim 10, wherein the conditions precedent include predetermined time intervals.

12. The shielding system of claim 10, wherein the conditions precedent include a determination that an RF matching network providing power to generate and maintain a plasma has optimal power coupling to the plasma.

13. The shielding system of claim 10, wherein the command signals generated by the incremental command circuit close selected ones of the plural switches so as to cause a progressively increasing portion of the plural shield segments to be connected to ground potential via the common node.

14. A plasma reactor for use in applying energized plasma to semiconductor articles, the plasma reactor comprising:

a reactor body, at least a portion of the reactor body being formed of a dielectric material;

an RF antenna disposed adjacent the reactor body;

an RF matching network connected to the RF antenna to couple energy to the RF antenna; and

a shield having variable shielding efficiency, disposed between the RF antenna and the reactor body;

wherein a semiconductor article disposed in the reactor body is processed by plasma that is energized by the RF antenna.

15. The plasma reactor of claim 14, wherein the shield comprises:

a substrate;

a common node disposed on the substrate;

plural shield segments spaced apart from one another and being disposed on the substrate; and

plural switches, each of the plural switches being connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node.

16. The plasma reactor of claim 14, wherein the portion of the reactor body being formed of a dielectric material comprises a lid formed of ceramic material.

17. The plasma reactor of claim 14, wherein the shield comprises:

a conductive plate; and

a switch connected between the conductive plate and ground potential, so that closure of the switch connects the conductive plate to ground potential.

18. The plasma reactor of claim 14, wherein the shield comprises:

a conductive plate;

an impedance element connected to ground potential; and

a switch connected between the conductive plate and the impedance element, so that closure of the switch connects the conductive plate, via the impedance element, to ground potential.

19. The plasma reactor of claim 14, wherein the shield comprises:
a conductive plate;
a variable impedance element connected between the conductive plate and ground potential.

20. A plasma reactor for use in applying energized plasma to semiconductor articles, the plasma reactor comprising:
a reactor body;
an RF antenna disposed adjacent the reactor body;
an RF matching network connected to the RF antenna to couple energy to the RF antenna; and
a shield having variable shielding efficiency, disposed between the RF antenna and the reactor body;
wherein a semiconductor article disposed in the reactor body is processed by plasma that is energized by the RF antenna;
wherein the shield comprises:
a substrate;
a common node disposed on the substrate;
plural shield segments spaced apart from one another and being disposed on the substrate; and
plural switches, each of the plural switches being connected between the common node and a respective one of the plural shield segments, so that closure of the switch connects its respective one of the plural shield segments to the common node; and
wherein the plural shield segments are arranged radially in a “pie slice” configuration and the common node extends circumferentially about the radially-arranged plural shield segments.

21. A method of shielding:

providing a shield having a variable shielding efficiency;
setting the shielding efficiency at a minimum value; and
incrementally increasing the shielding efficiency of the shield.

22. The method of shielding of claim 21, wherein the shielding efficiency is incrementally increased, subsequent to a previous incrementing of the shielding efficiency, only when an RF matching network has successfully optimized power coupling to a plasma disposed near the shield.

23. The method of shielding of claim 21, wherein the shielding efficiency is incrementally increased after a plasma strike has been achieved to establish a plasma disposed near the shield.

24. A method of etching a semiconductor article:
placing the semiconductor article in a plasma etch chamber
setting the shielding efficiency of a shield to a minimum value
striking a plasma about the semiconductor article
increasing the shielding efficiency of the shield from the minimum value to a maximum value

25. A method of retrofitting a variable efficiency electrical shield to a semiconductor process chamber surrounded by an RF antenna:
providing a variable efficiency electrical shield;
installing the shield between the process chamber and the RF antenna;
interfacing the shield to a process controller to establish control of the efficiency of the shield.